

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A camera comprising:
a main body;
an eyepiece;
a switching unit;
an image receiver; and
a display having a semiconductor device,
wherein the semiconductor device comprises:
a gate electrode formed over a substrate;
a first insulating layer formed over the gate electrode;
a second insulating layer formed over the first insulating layer;
a semiconductor layer formed over the second insulating layer, the
semiconductor layer having at least a channel region and at least one impurity region;
an inorganic insulating layer formed over the semiconductor layer, the inorganic
insulating layer being in contact with a portion of the impurity region; and
an organic insulating layer formed over the inorganic insulating layer, the organic
insulating layer being in contact with another portion of the impurity region.
2. (Original) A camera according to claim 1, wherein the gate electrode
comprises at least one layer comprising a material selected from the group consisting of
tantalum, molybdenum, titanium, chromium and silicon.
3. (Currently Amended) A camera comprising:
a main body;

~~an eyepiece;~~

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

a gate electrode formed over a substrate;

a first insulating layer comprising silicon nitride formed over the gate electrode;

a second insulating layer comprising silicon oxide formed over the first insulating layer;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

4. (Original) A camera according to claim 3, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

5. (Currently Amended) A camera comprising:

a main body;

~~an eyepiece;~~

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode, the first insulating layer having a thickness of 10-200nm;

a second insulating layer formed over the first insulating layer, the second insulating layer having a thickness of 50-300nm;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

6. (Original) A camera according to claim 5, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

7. (Currently Amended) A camera comprising:

a main body;

~~an eyepiece;~~

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode;

a second insulating layer formed over the first insulating layer;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer comprising silicon oxide formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

8. (Original) A camera according to claim 7, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

9. (Currently Amended) A camera comprising:

a main body;

~~an eyepiece;~~

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

at least two gate electrodes formed over a substrate;

a first insulating layer formed over the gate electrodes;

a second insulating layer formed over the first insulating layer;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

10. (Original) A camera according to claim 9, wherein each of the gate electrodes comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

11. (Currently Amended) A camera comprising:
a main body;
~~an eyepiece;~~
a switching unit;
an image receiver; and
a display having a driving circuit and a pixel circuit,
wherein a plurality of thin film transistors formed in the pixel circuit, each of the thin film transistors comprising:
a gate electrode formed over a substrate;
a first insulating layer formed over the gate electrode;
a second insulating layer formed over the first insulating layer;
a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;
an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region; and
an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

12. (Original) A camera according to claim 11, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

13. (Original) A semiconductor device comprising:
a gate electrode formed over a substrate;

- a first insulating layer formed over the gate electrode;
- a second insulating layer formed over the first insulating layer;
- at least a channel region and an impurity region formed over the second insulating layer;
- an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and
- an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

14. (Original) A semiconductor device according to claim 13, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

15. (Original) A semiconductor device according to claim 13, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.

16. (Original) A semiconductor device comprising:

- a gate electrode formed over a substrate;
- a first insulating layer comprising silicon nitride formed over the gate electrode;
- a second insulating layer comprising silicon oxide formed over the first insulating layer;
- at least a channel region and an impurity region formed over the second insulating layer;

an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

17. (Original) A semiconductor device according to claim 16, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

18. (Original) A semiconductor device according to claim 16, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.

19. (Currently Amended) A semiconductor device comprising:

a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode, the first insulating layer having a thickness of 10-200nm;

a second insulating layer formed over the first insulating layer, the second insulating layer having a thickness of 50-300nm;

a channel region and an impurity ~~regions~~ region formed over the second insulating layer;

an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

20. (Original) A semiconductor device according to claim 19, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

21. (Original) A semiconductor device according to claim 19, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.

22. (New) A camera according to claim 1, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

23. (New) A camera according to claim 3, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

24. (New) A camera according to claim 5, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

25. (New) A camera according to claim 7, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

26. (New) A camera according to claim 9, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

27. (New) A camera according to claim 11, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

28. (New) A semiconductor device according to claim 13, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

29. (New) A semiconductor device according to claim 16, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.

30. (New) A semiconductor device according to claim 19, wherein the semiconductor device further comprises a pixel electrode formed over the organic insulating layer.